

Abstract

A non-volatile SRAM memory cell and a non-volatile semiconductor memory device capable of programming SRAM data in a SRAM (15) to a non-volatile memory unit (16) through fast operation of the SRAM (15) are disclosed. A non-volatile semiconductor memory device (1) can achieve reduction in a voltage necessary for a programming operation to program SRAM data to the non-volatile memory unit (16). Thus, a first access transistor (21a), a second access transistor (21b), a first load transistor (22a), a second load transistor (22b), a first drive transistor (23a), and a second drive transistor (23b) included in the SRAM (15) connected with the non-volatile memory unit (16) can each include a gate insulating film having a thickness less than or equal to 4 nm, which achieves fast operation of the SRAM (15) at a lower power supply voltage.